

Notice of References Cited	Application/Control No. 10/516,380		Applicant(s)/Patent Under Reexamination MAKIMOTO ET AL.	
	Examiner Tram H. Nguyen		Art Unit 2818	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-2002/0195619	12-2002	Makimoto et al.	257/197
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
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	I	US-			
	J	US-			
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FOREIGN PATENT DOCUMENTS

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	N					
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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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